



A division of



# Dual Beam nSec Annealing for MOL & BEOL Applications

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- > July 2018

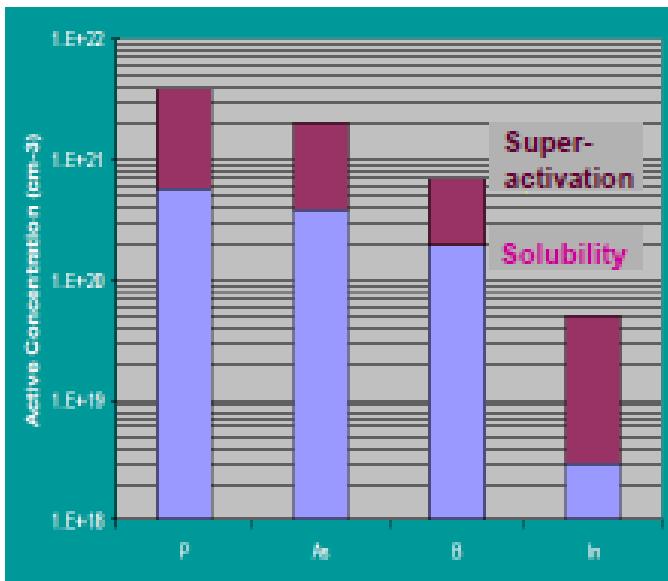
# Outline

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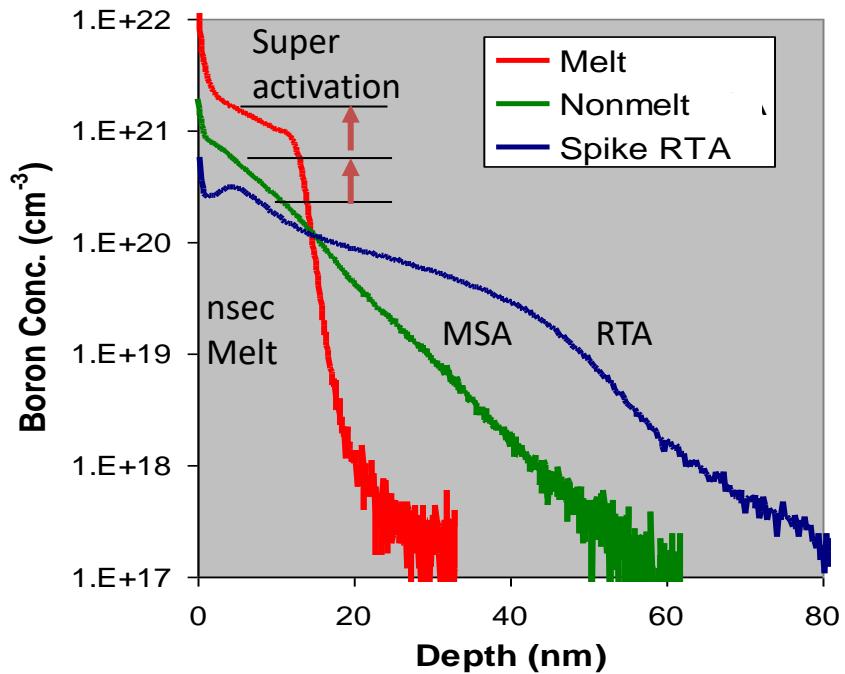
- Dual beam nSec annealing technology
- Applications in MOL
- Applications in BEOL

# Benefits for nSec Melt Annealing

## Super Activation

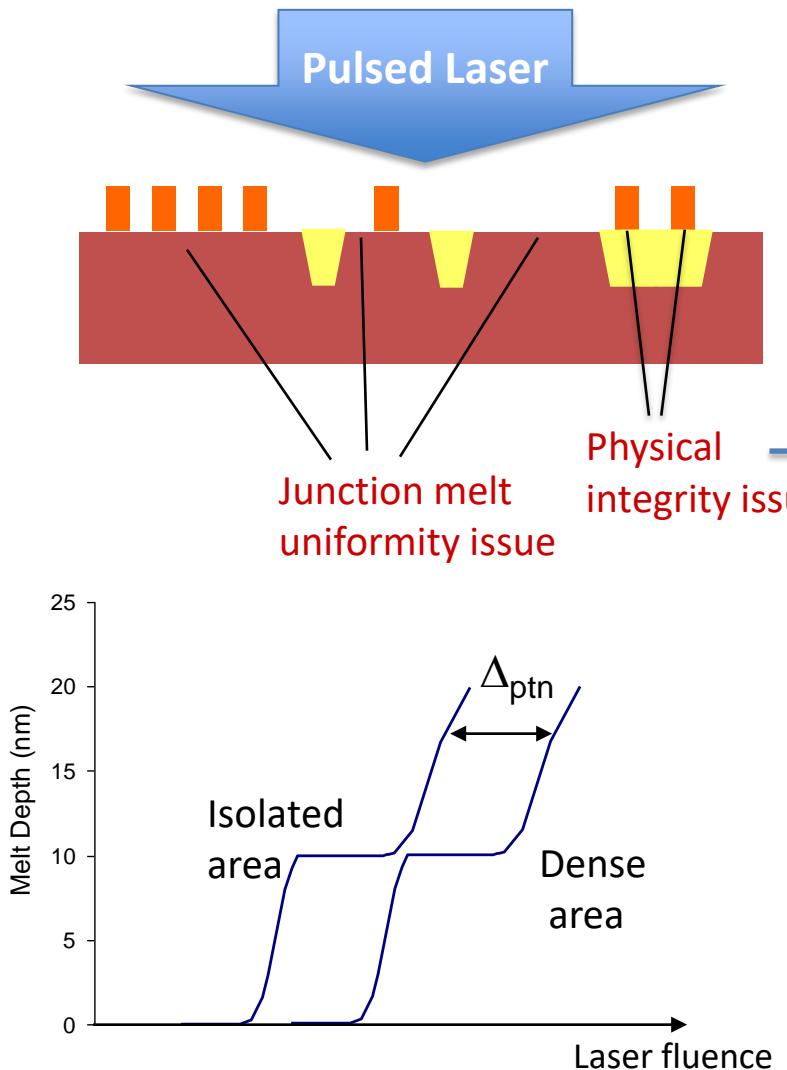


## Junction Profile

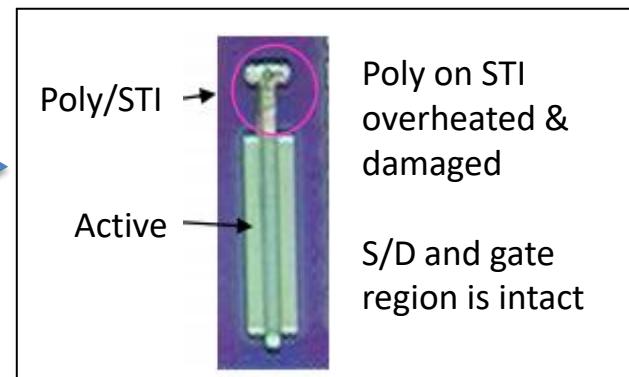


- Super activation above solid solubility
- Ultra-shallow, box-like abrupt junction

# Conventional nSec Melt Annealing Challenges

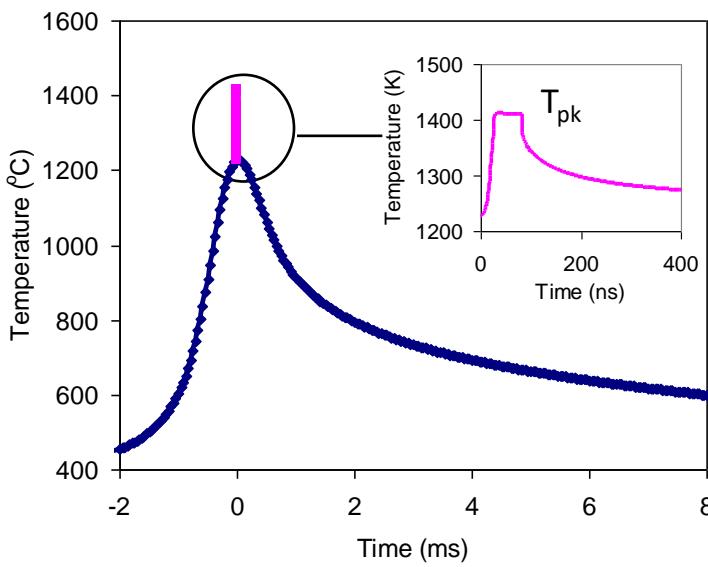
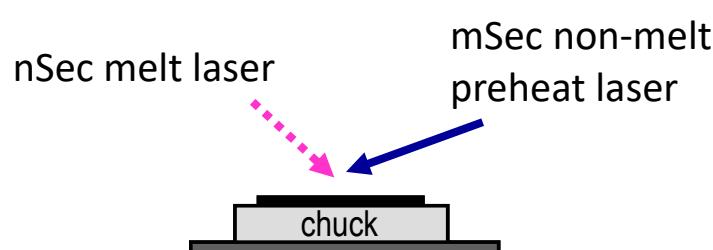


- Non-uniform optical absorption
- Inhomogeneous thermal properties



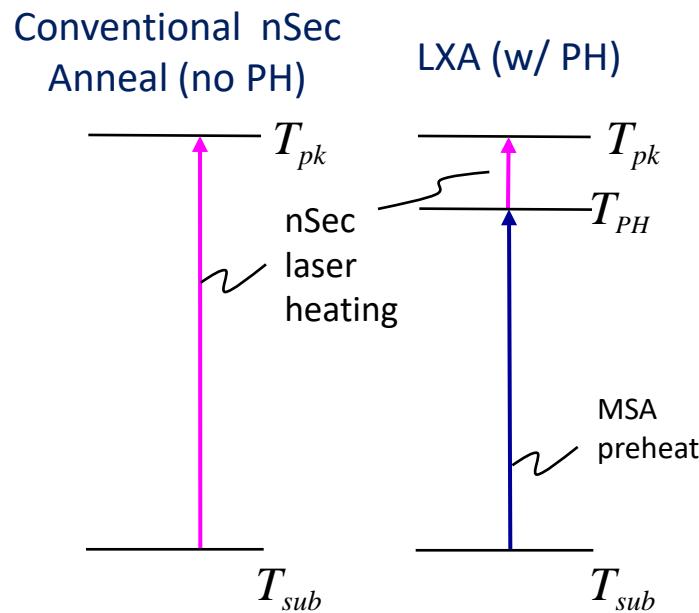
- Severe pattern effect
- Very small or no process window
- Gate on oxide physical integrity also a concern

# Dual Beam nSec Technology Advantages



$$\Delta T_{LXA} \approx \Delta T_{ns} = \left( \frac{T_{pk} - T_{PH}}{T_{pk} - T_{sub}} \right) \cdot \Delta T_{LTA}$$

Reduction factor /

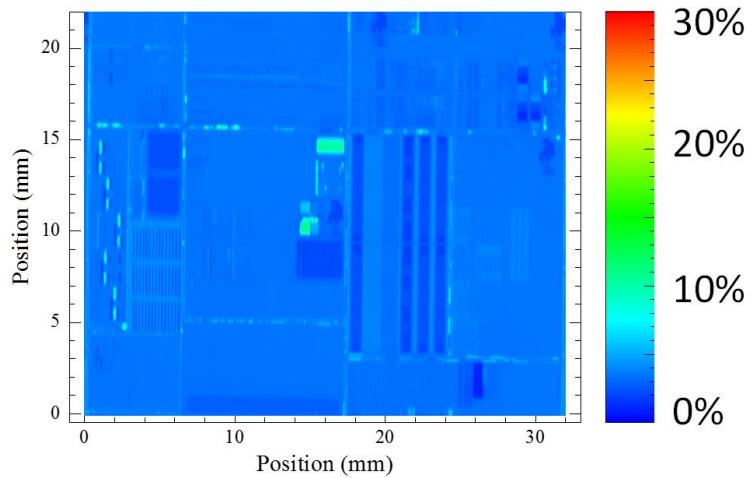


- mSA provides low thermal budget & uniform heating
- nSec spike on top of MSA raises T to melt
- Pattern effect is significantly improved

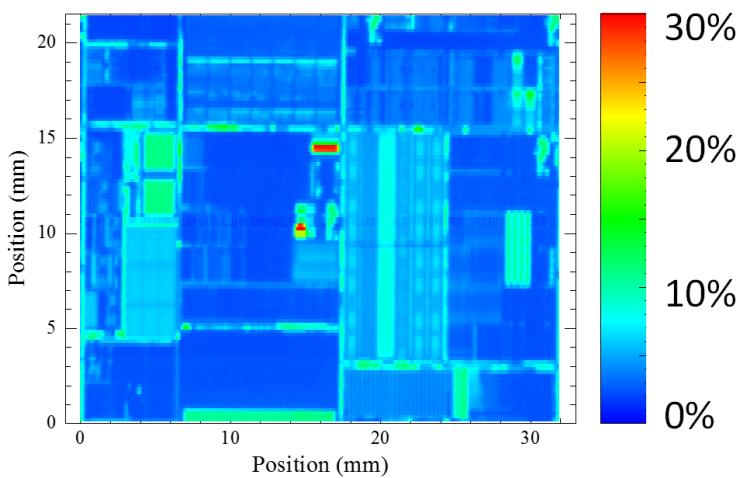
# Optical Pattern Effects

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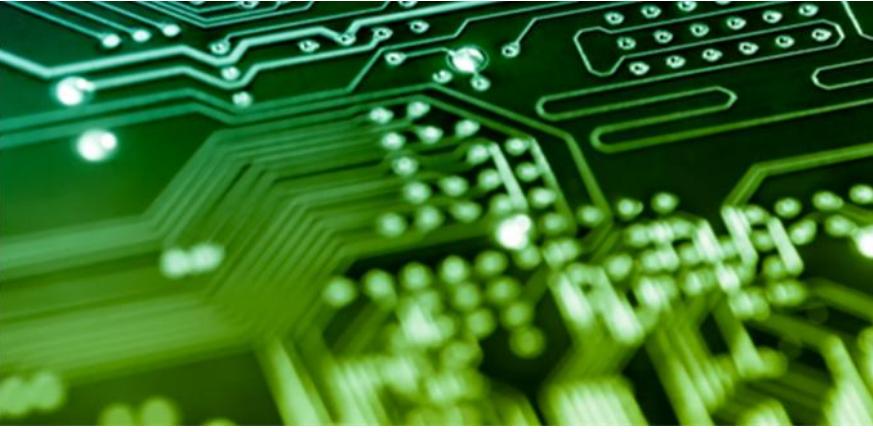
Pre-heat reflectance



532nm reflectance



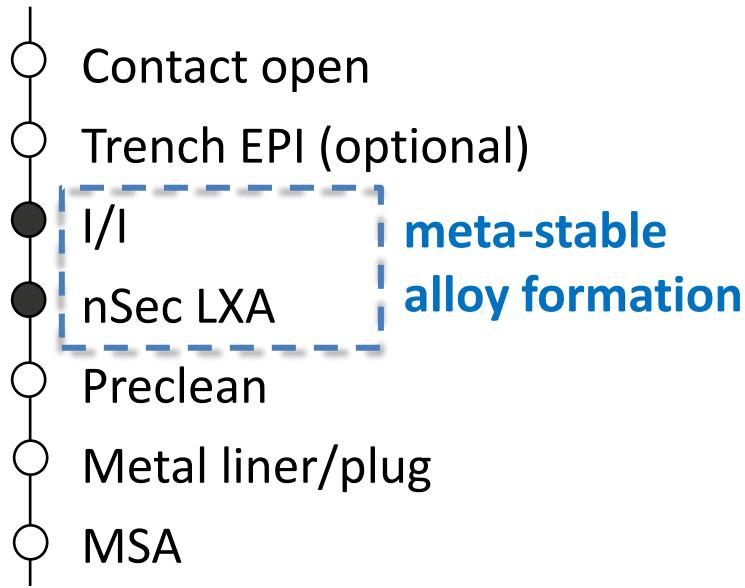
- 532 shows more optical pattern effects
- PH laser enables significant reduction of pattern effects



# nSec Anneal for MOL Applications

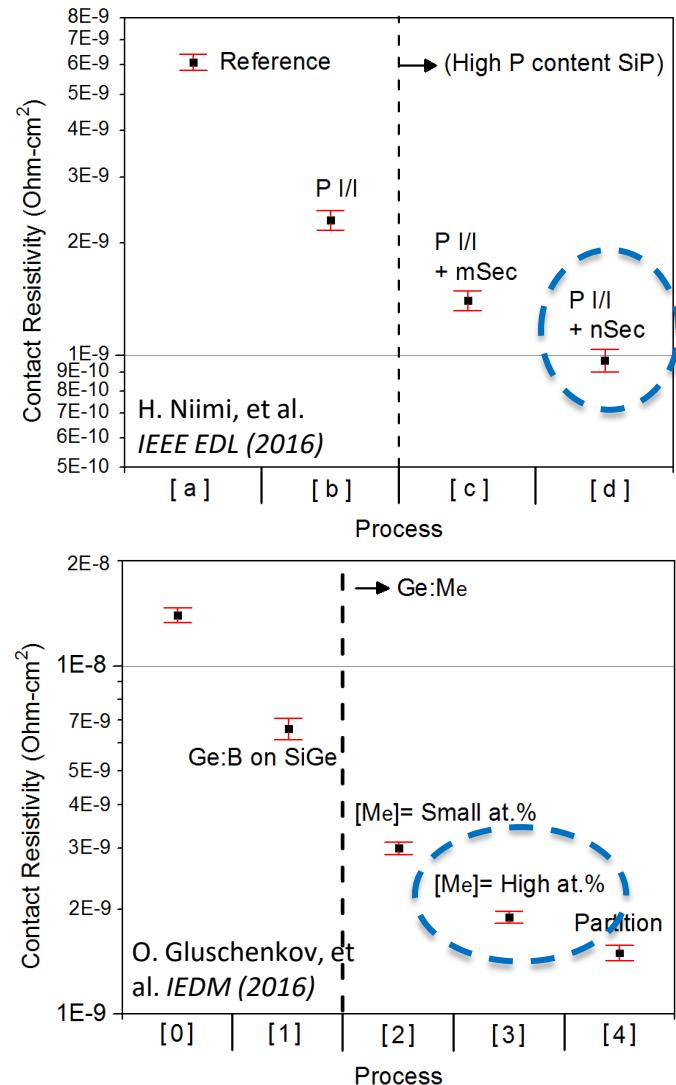


# MOL Application – Contact Rc Reduction

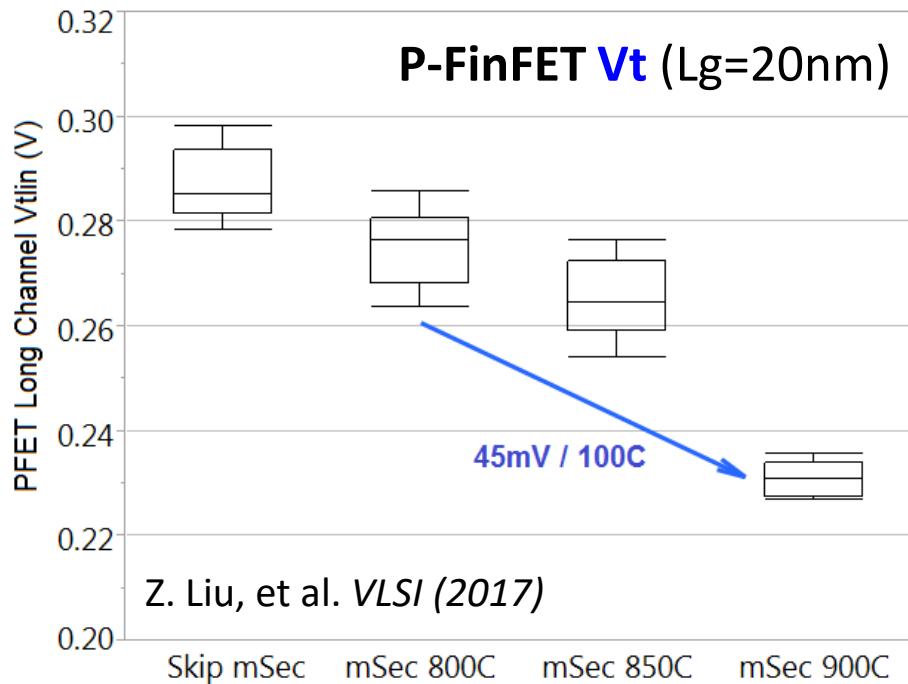
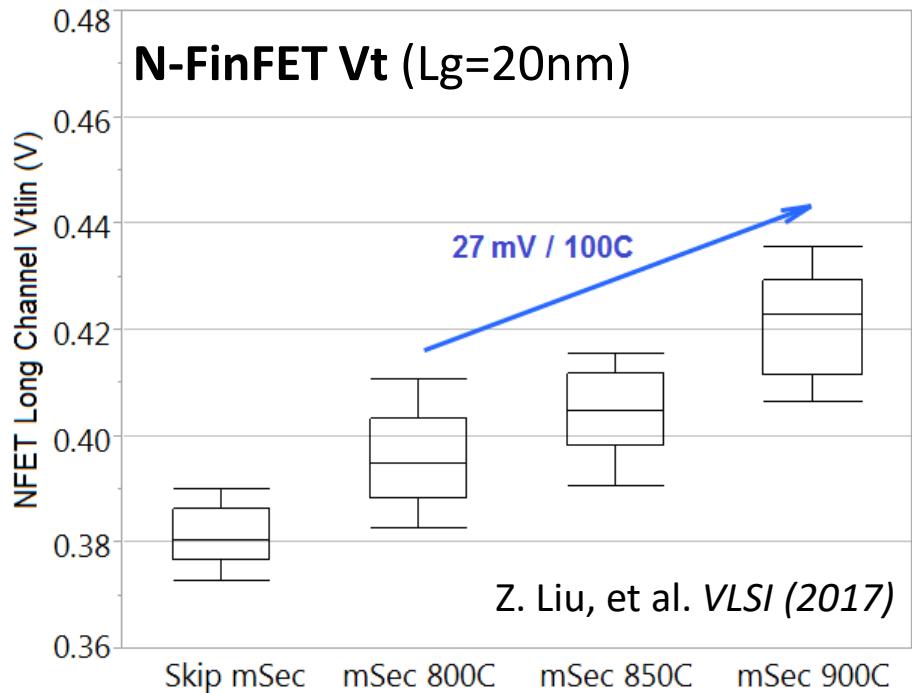


IBM Alliance record results:

- $\rho_c < 1 \times 10^{-9} \Omega\text{-cm}^2$  achieved for N contact
- $\rho_c < 2 \times 10^{-9} \Omega\text{-cm}^2$  achieved for P contact

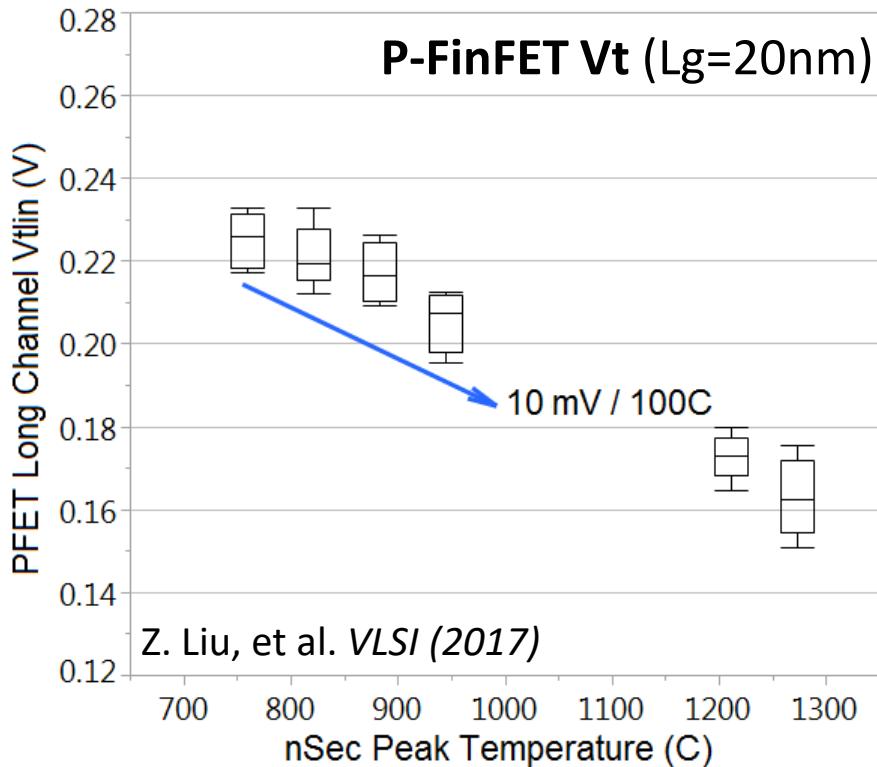
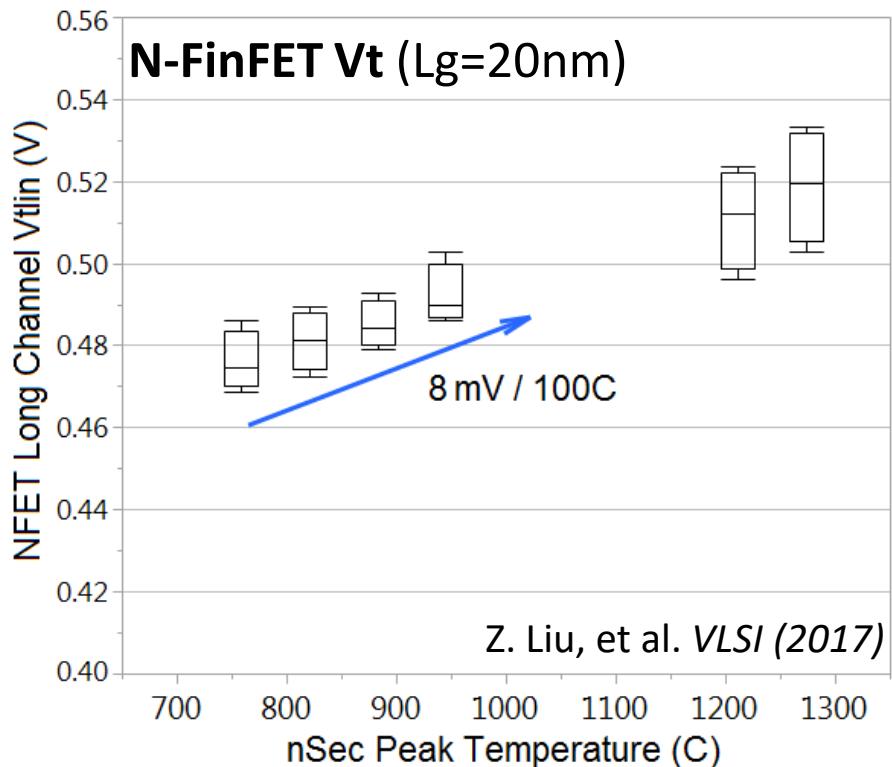


# mSec MSA Impact on V<sub>t</sub>

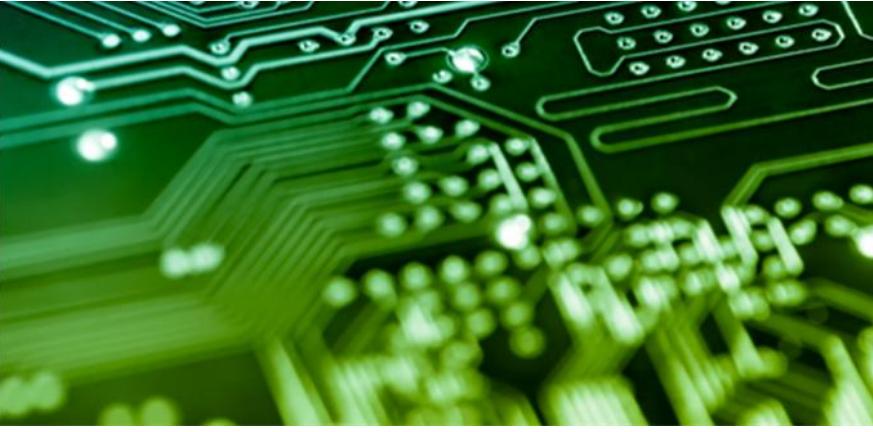


- V<sub>t</sub> is sensitive to MSA temperature
- Pattern effect further limits MSA process window

# nSec LXA Impact on V<sub>t</sub>



- nSec LXA has very low thermal budget
- 3~4X less impact on V<sub>t</sub> than mSec anneals

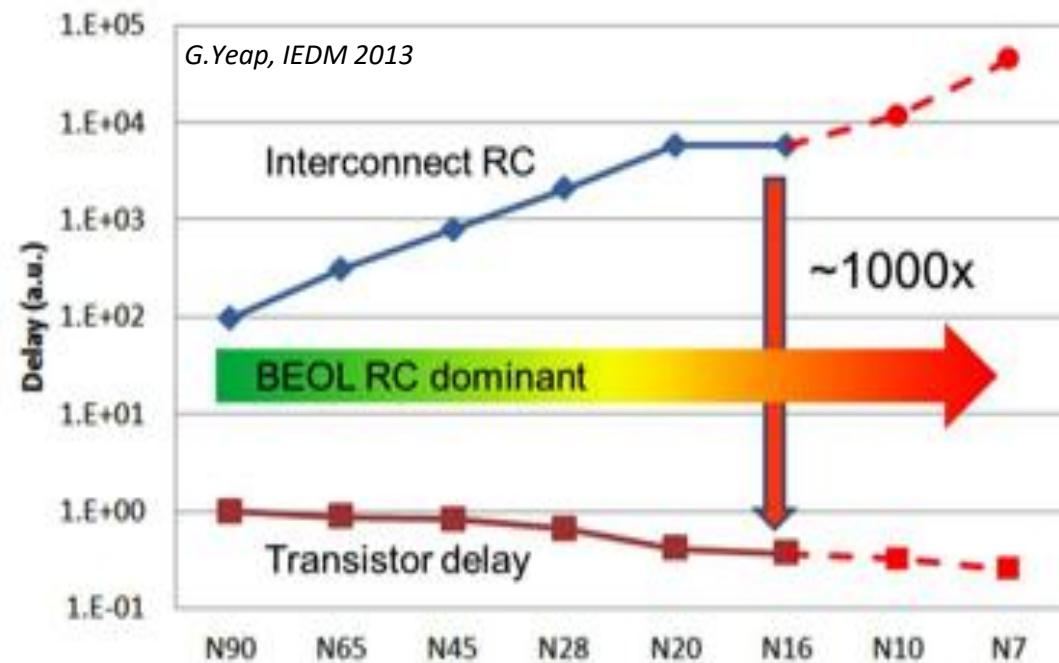


# nSec Anneal for BEOL Applications



# Key Issue in the Industry – BEOL RC Delay

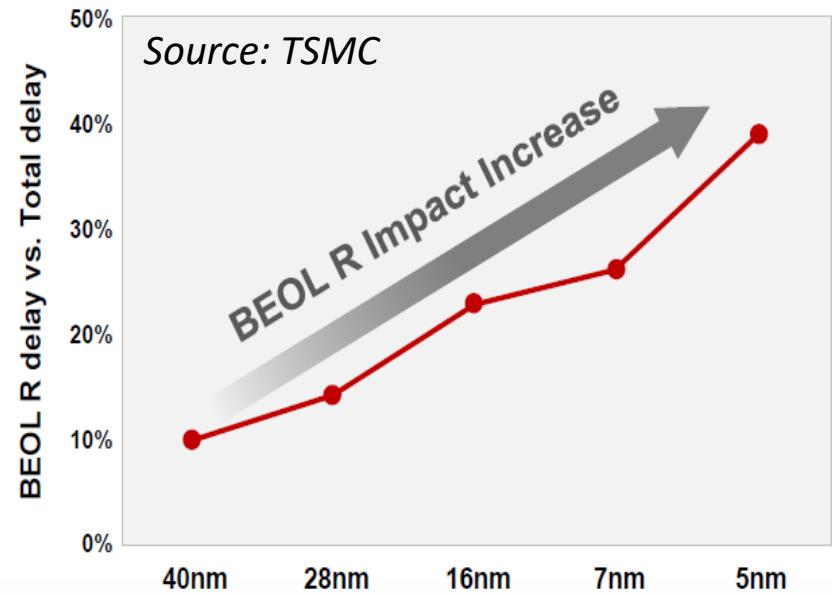
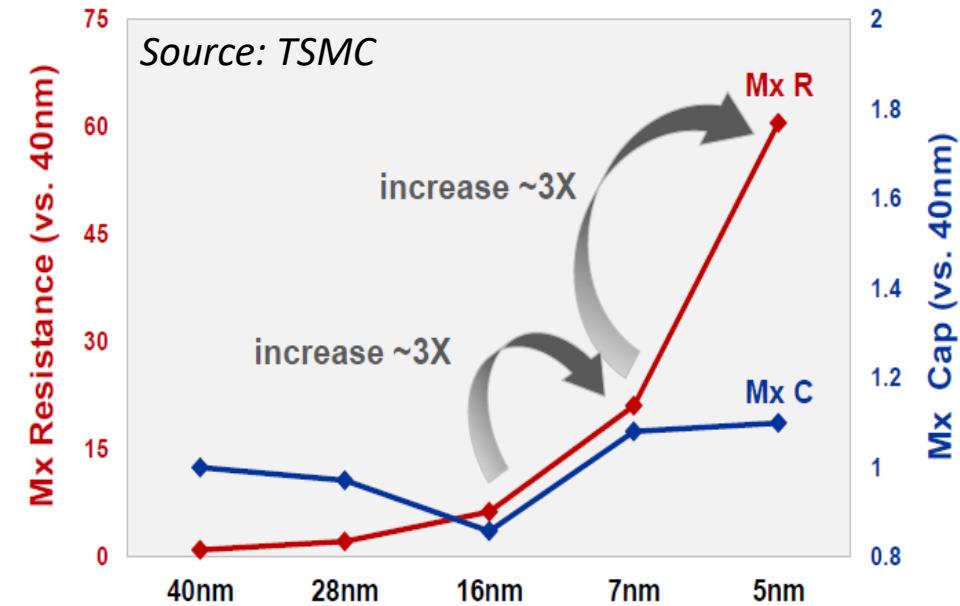
*“BEOL performance/area/cost is the foremost issue for 10/7 nm node” – G. Yeap (VP, QCOM) IEDM 2013*



- BEOL RC delay dominating
- Faster transistors don't matter w/o fast BEOL

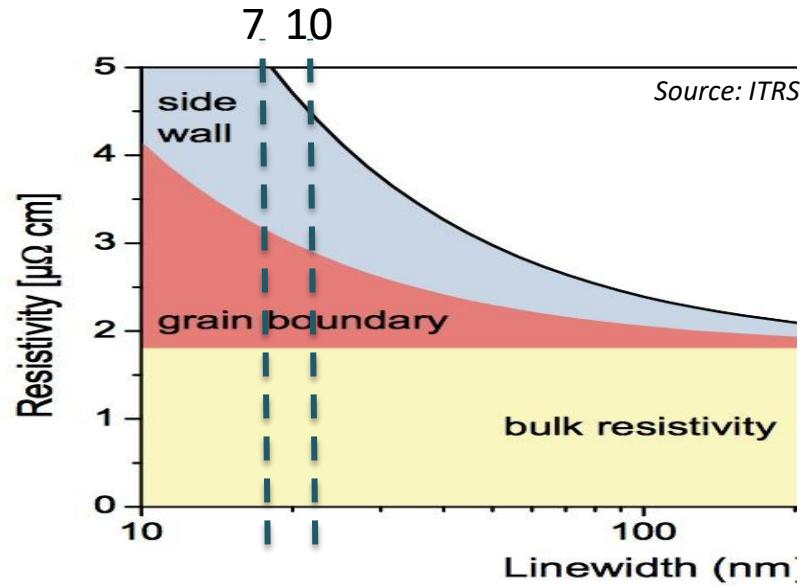
# Control of BEOL Resistance Is Most CRITICAL

R increase is the root cause



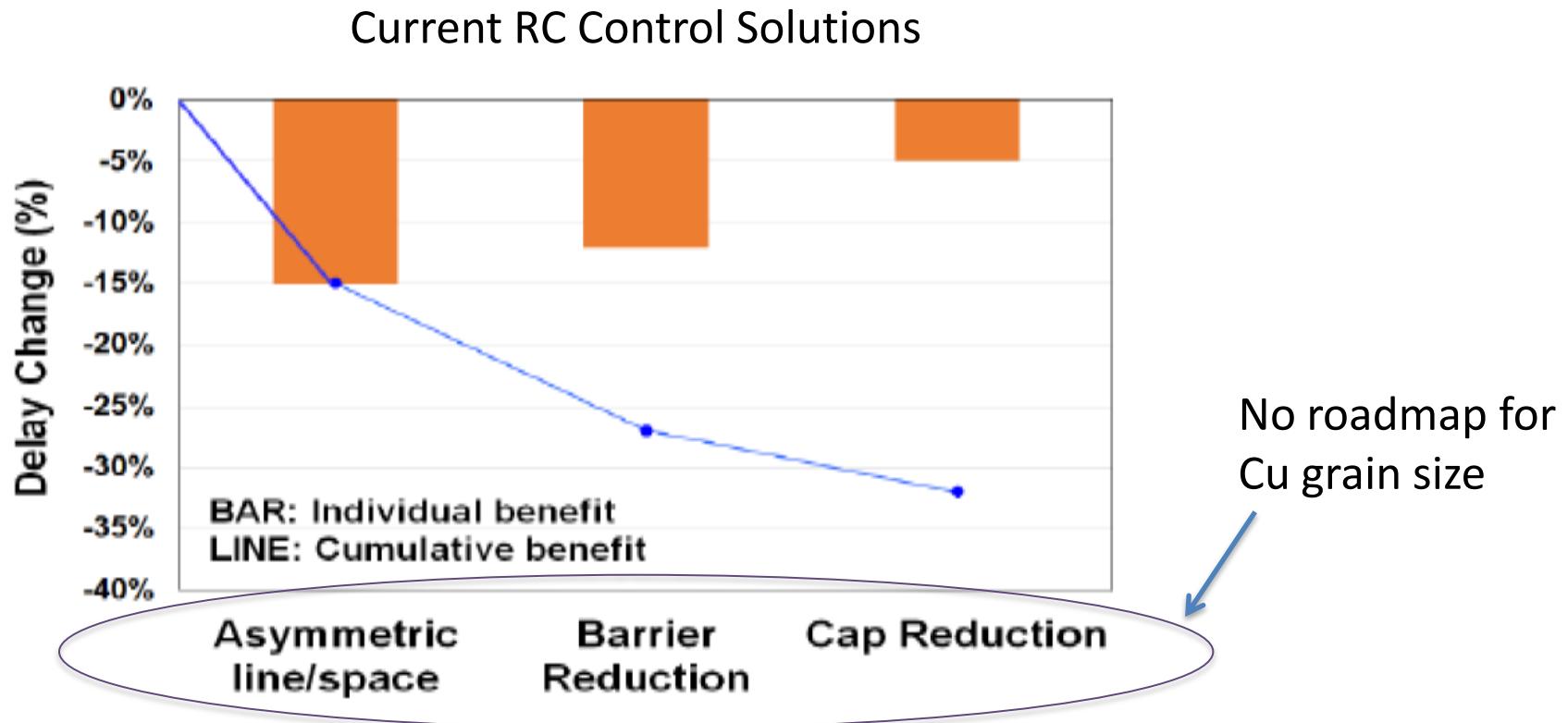
- Industry is in urgent demand to control/mitigate Mx R increase

# Root Causes for Cu R Skyrocketing



- Fine Cu grains → More grain boundaries → sharp R increase for narrow lines

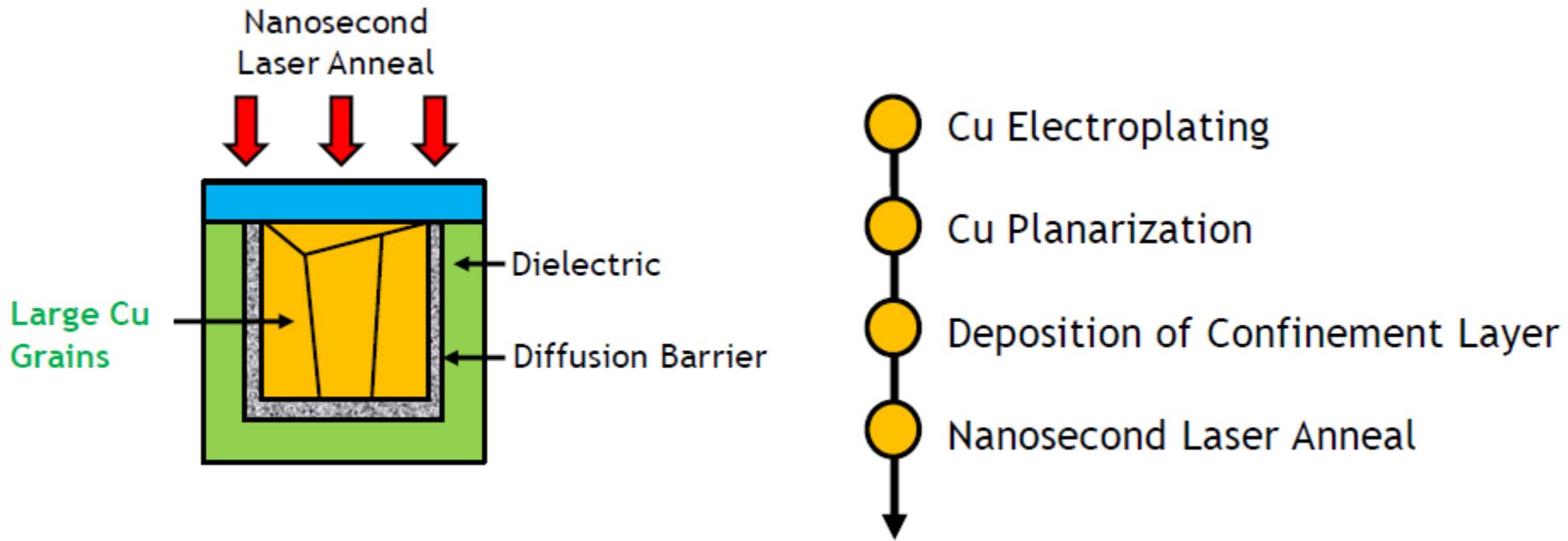
# Current Cu RC Delay Improvement Schemes



- Enlarging Cu grain, as an effective R reduction method, has been OVERLOOKED before

# Process Flow

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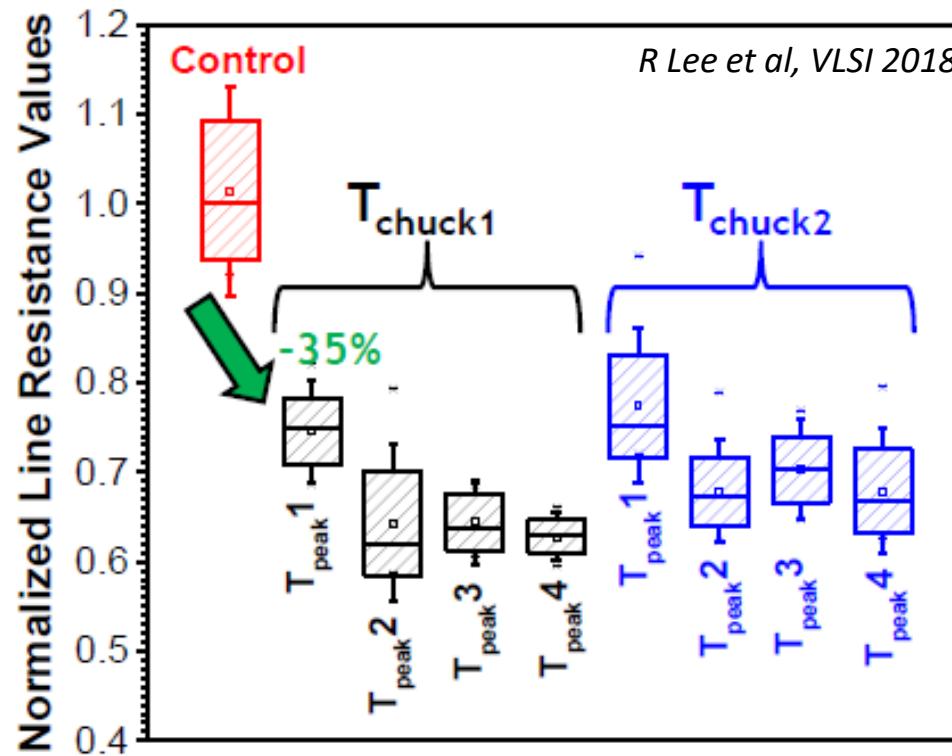
- Processed with 14nm BEOL process flow to 10+ Mx

# Key Metrics for Evaluation

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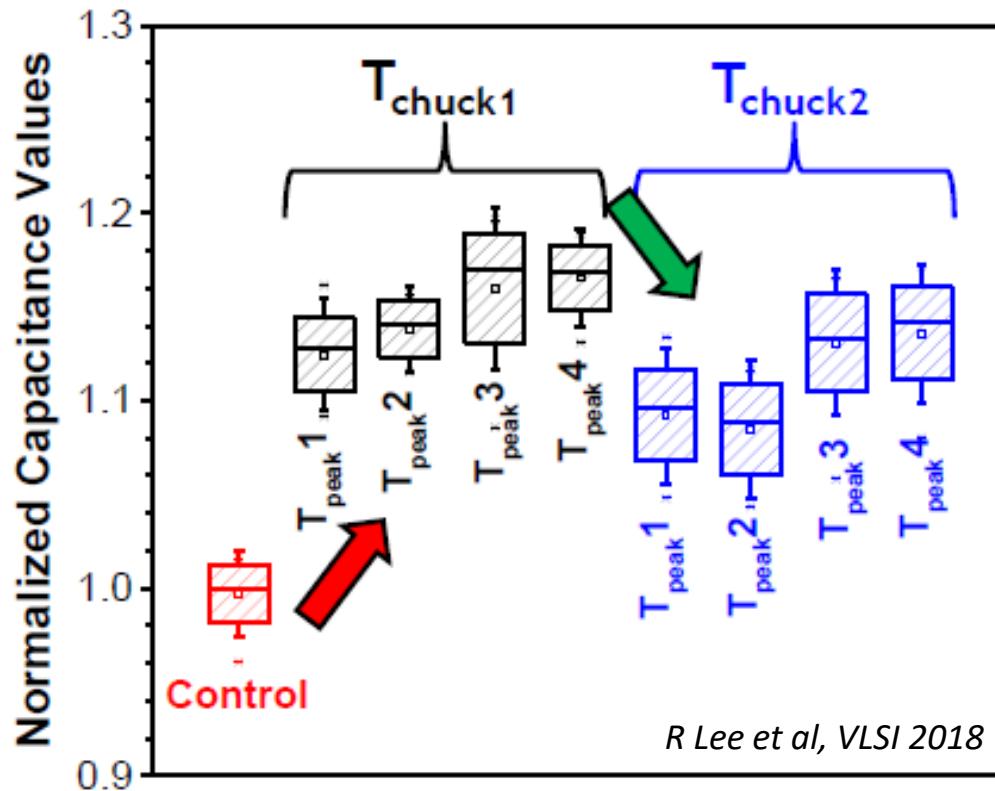
- Key Metrics include;
  - Cu line resistance
  - M1 capacitance
  - RC performance
  - Cu Grain Size
  - Impact on FEOL FETs
  - Reliability ( $V_{BD}$ , EM Lifetime)

# Cu Line Resistance



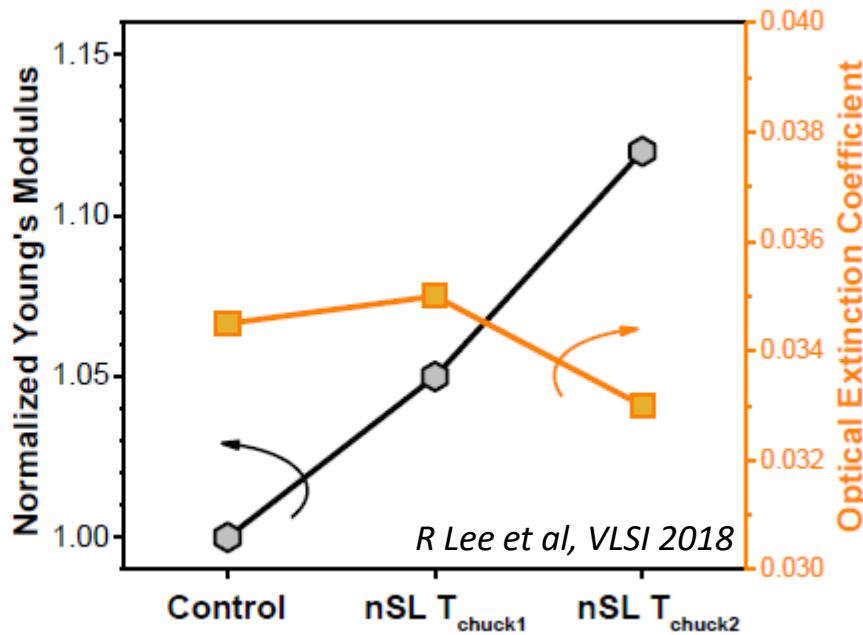
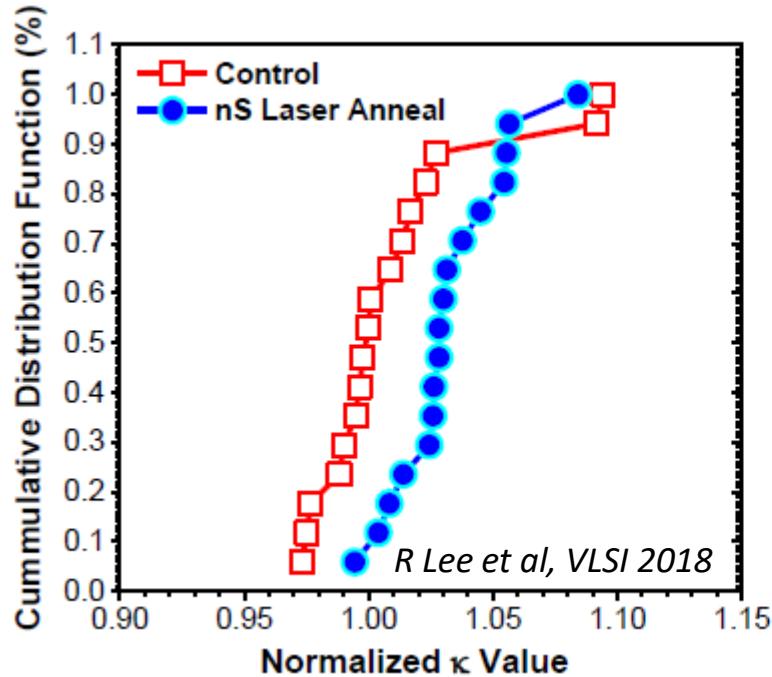
- nSec enables 35% R reduction

# M1 Capacitance after nSec Anneal



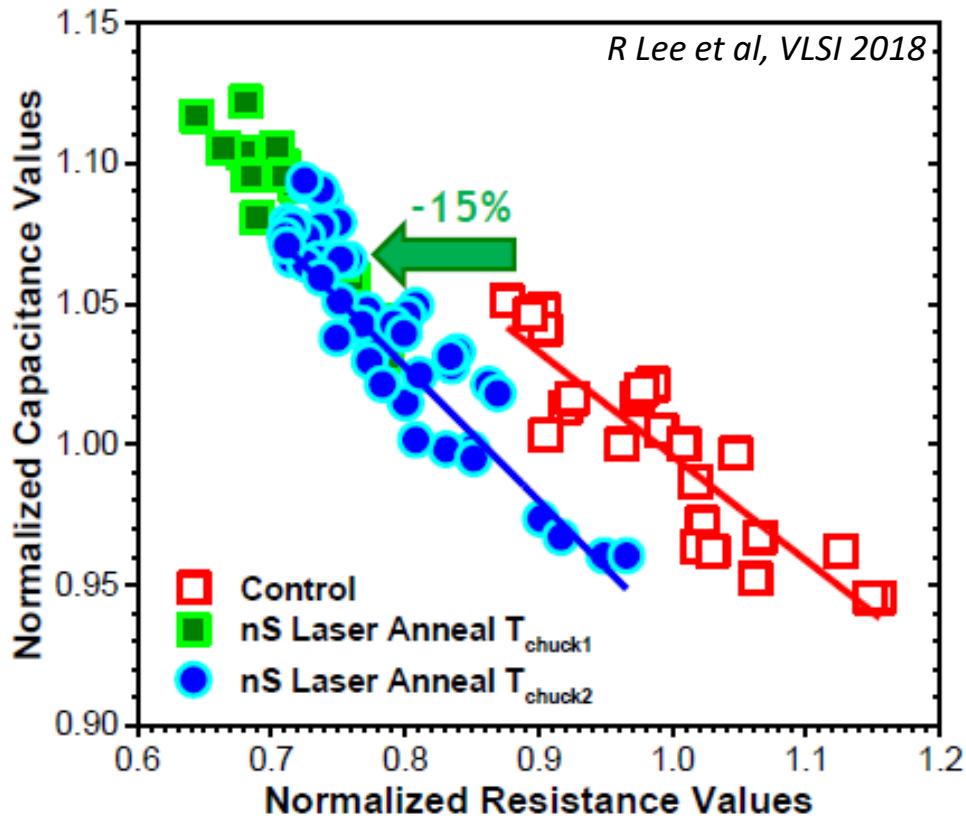
- ULK capacitance increase 9% after nSec anneal
- Plans available to improve capacitance

# nSec Anneal Impact on ULK



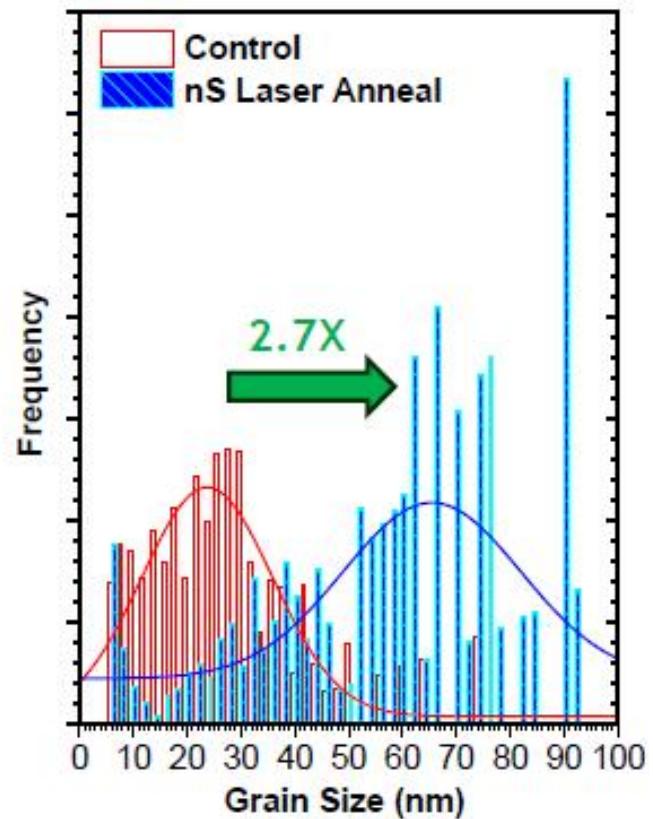
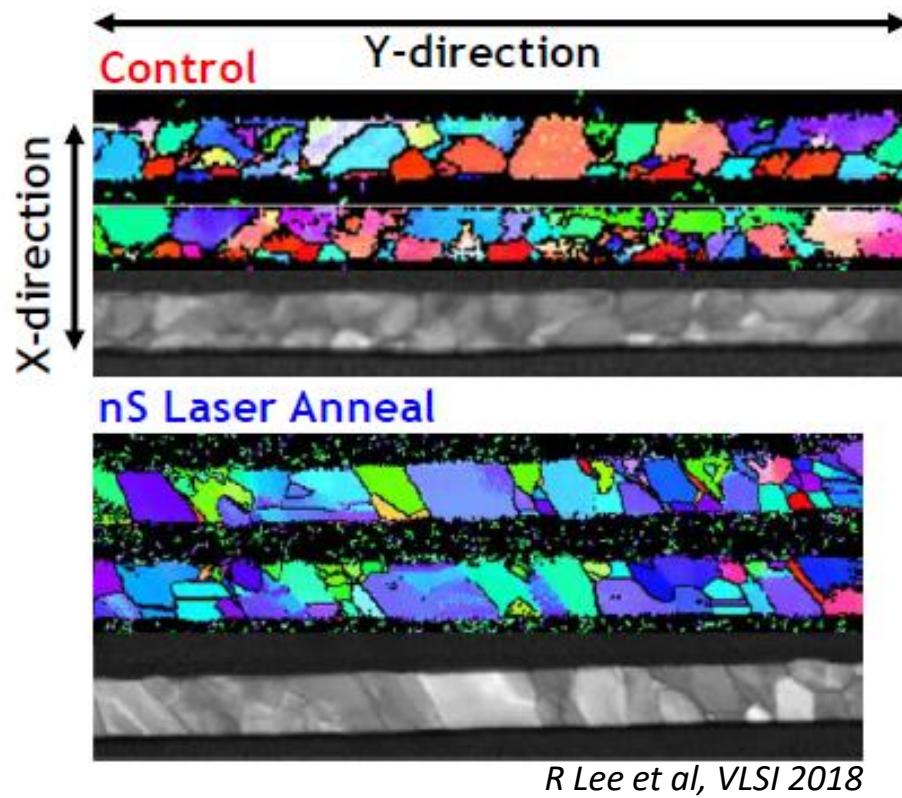
- $\kappa$  value increases ~3%
- Young's modulus improves ~12%

# RC Improvement w/ nSec Anneal



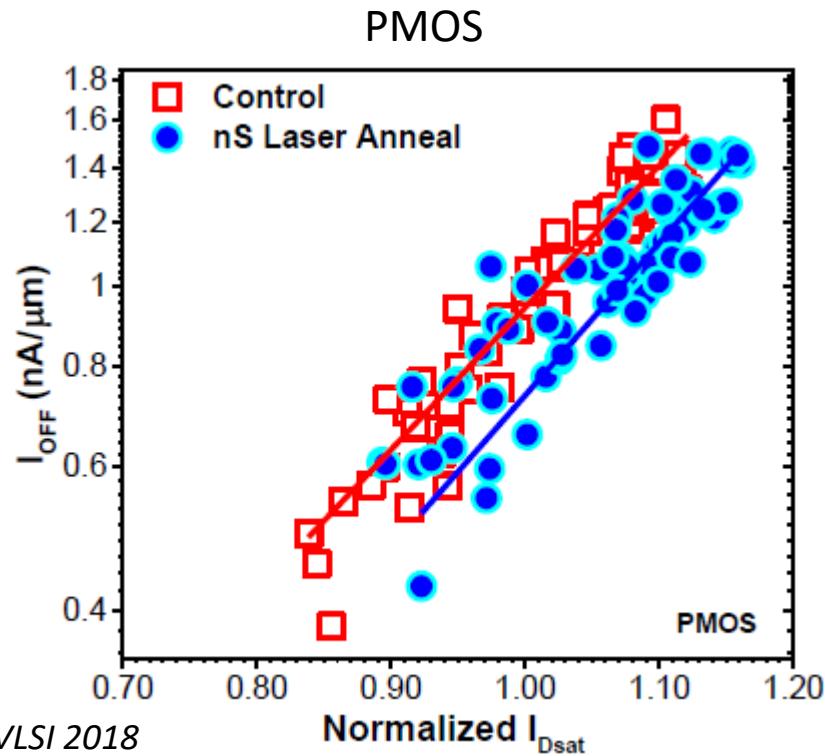
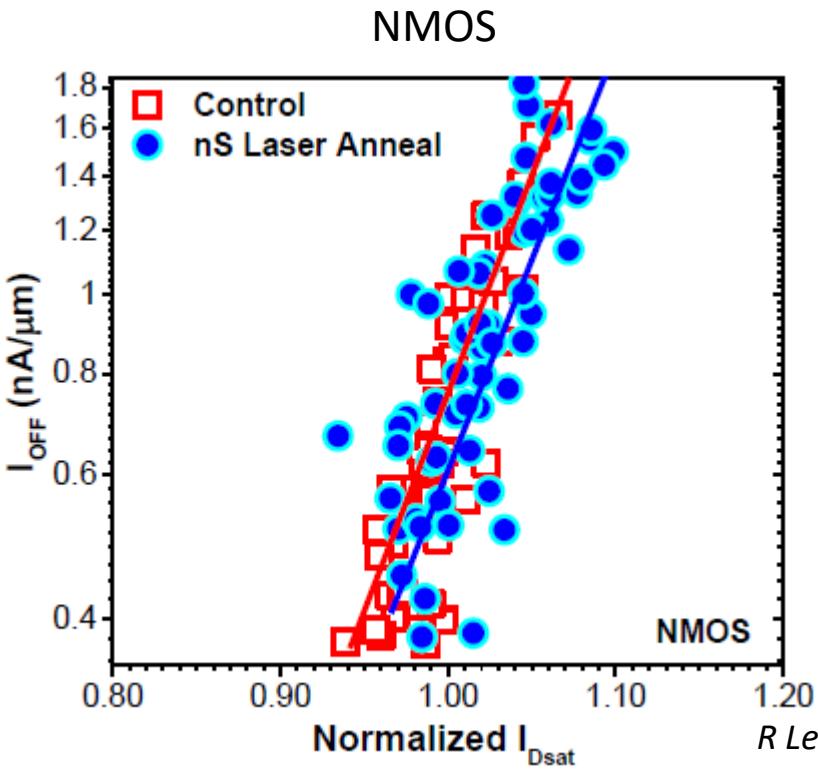
- An impressive -15% RC improvement is achieved

# Cu Grains after nSec Anneal



- 2.7X larger grains
- More bamboo like structures

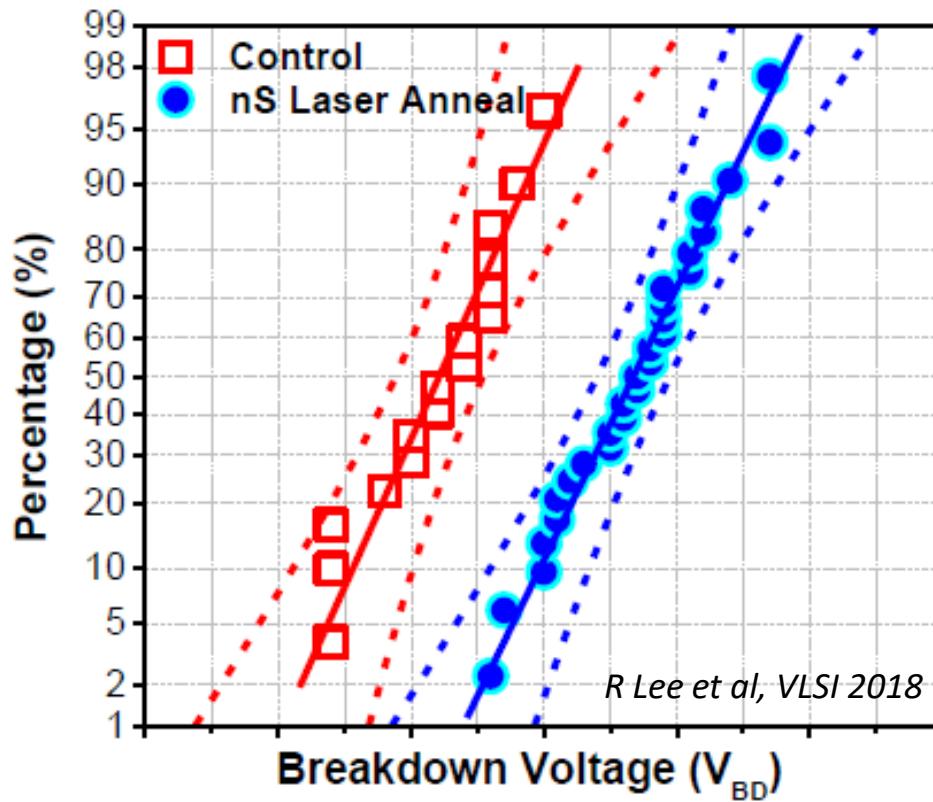
# nSec Cu Anneal Impact on Devices



R Lee et al, VLSI 2018

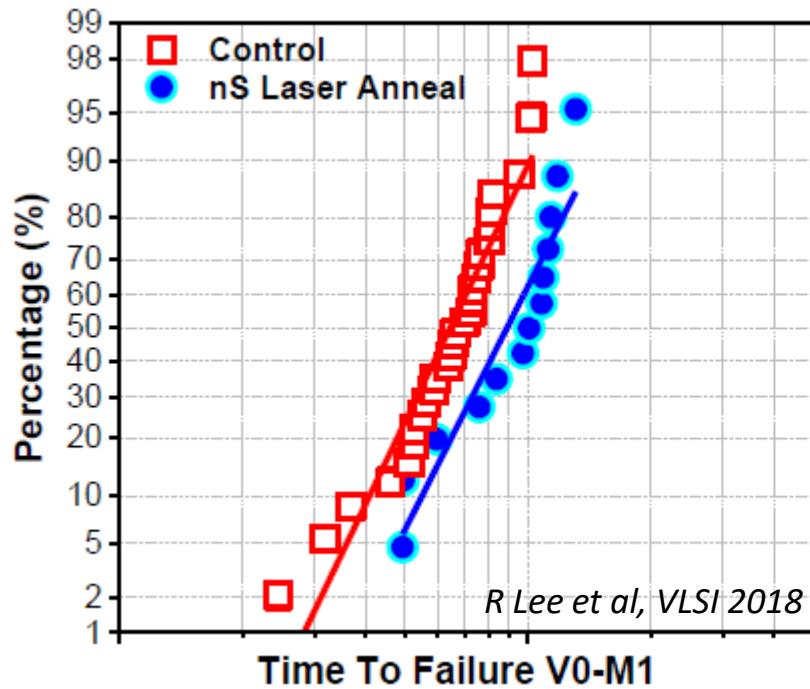
- +2% for NMOS
- +5% for PMOS

# M1-M1 Dielectric $V_{bd}$ after nSec Anneal

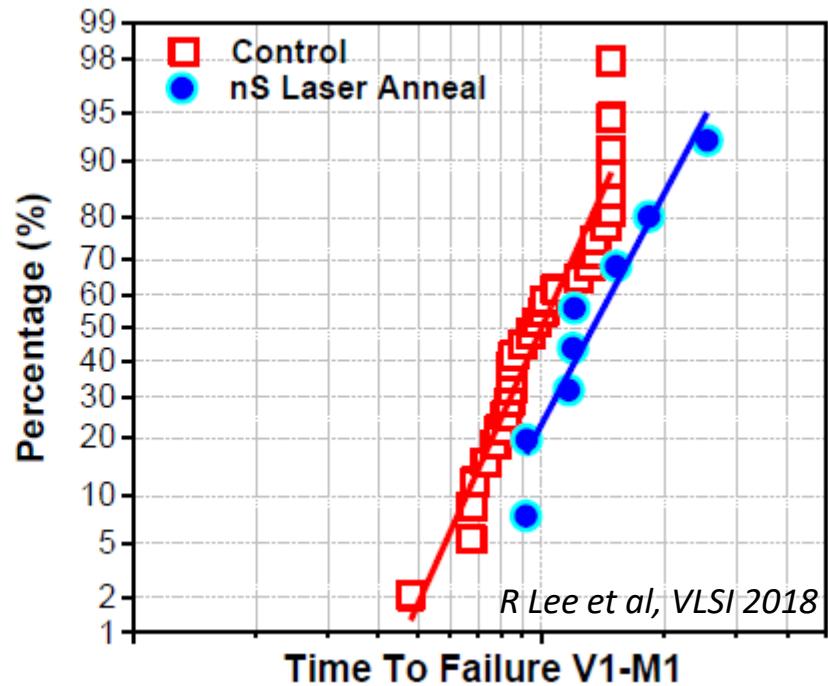


- 10% improvement, due to more interconnecting bonds

# EM Lifetime



R Lee et al, VLSI 2018



R Lee et al, VLSI 2018

- Comparable/better EM lifetime after anneal

# Summary

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Summary: nS Laser Anneal vs Conv. Anneal	
Parameters	Performance
Line Resistance	+ 35%
Capacitance	- 9% (tunable)
RC Performance	+ 15%
Median Cu Grain Size	+ 2.7X
N/PMOS $I_{DSS}$	+ 2%, +5%
M1-M1 Dielectric $V_{BD}$	+ 10%
V0-M1 EM Lifetime	+ 27%
V1-M1 EM Lifetime	+ 36%